

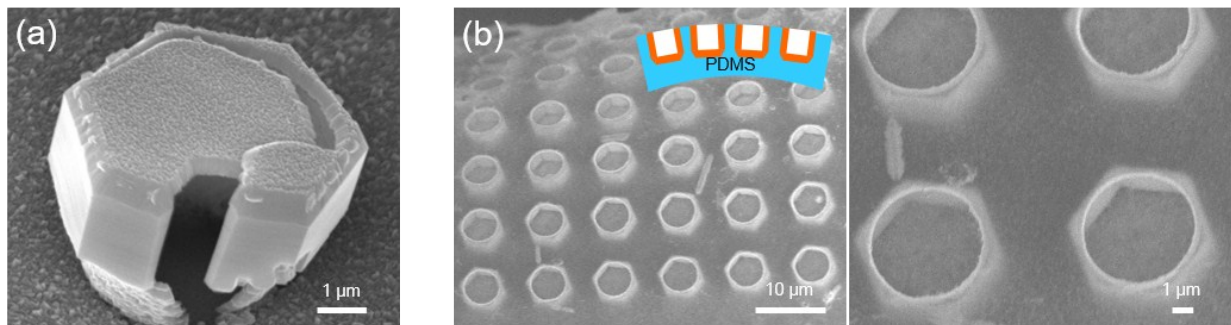
**ELECTRONIC SUPPLEMENTARY INFORMATION**

# Three-dimensionally-architected GaN light emitting crystals

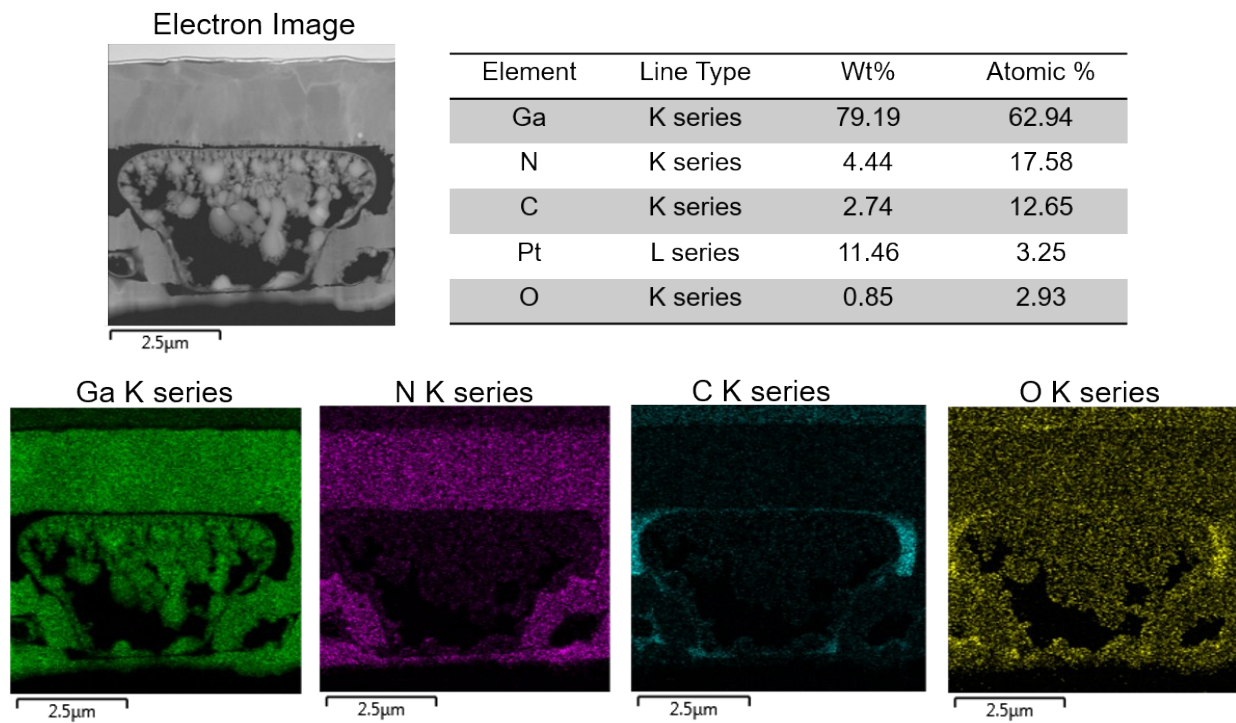
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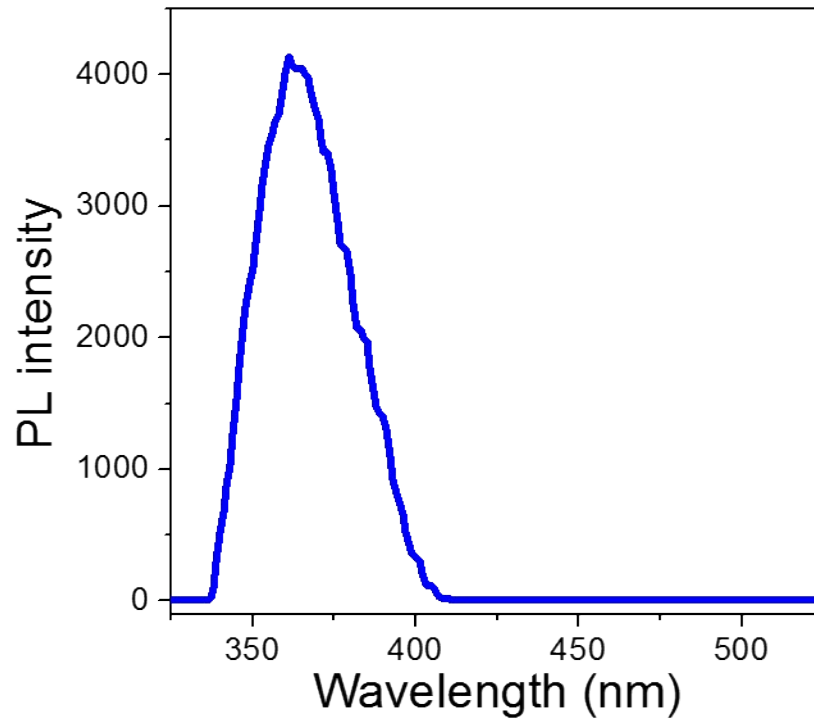
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**Figure S1.** (a) SEM image of broken GaN crystal. (b) SEM images of GaN crystal array embedded in PDMS and mechanically exploited from the substrate.



**Figure S2.** Top: TEM image (left panel) and corresponding EDS analysis result (right panel). Bottom: The corresponding elemental mapping images of Ga (green), N (purple), C (blue) and O (yellow).



**Figure S3.** Room temperature PL spectrum of n-type GaN crystals.